

	L #	Hits	Search Text	DBs	Time Stamp
✓ 1	L1	118	("6589890") or ("5685941") or ("6077353") or ("6110836") or ("6346489") or ("6313042") or ("6372301") or ("6207558") or ("6368880") or ("6908865") or ("5504043") or ("5961793") or ("6426282") or ("6420260") or ("5242860") or ("5378660") or ("5360996") or ("5434044") or ("5521120") or ("5759360") or ("5972178") or ("5919342") or ("6071811") or ("5925225") or ("5943600") or ("6207027") or ("5882399") or ("6045666") or ("6059872") or ("6149777") or ("6899799") or ("5622608") or ("5766379") or ("5911113") or ("5959358") or ("6057237") or ("6037257") or ("6692617") or ("6605197") or ("6139699") or ("6387805") or ("6887353") or ("6057223") or ("6174811") or ("6232665") or ("6235163") or ("6328871") or ("6399479") or ("6398929") or ("6488823") or ("6200433") or ("6458251") or ("6350353") or ("6160315") or ("6436267") or ("6582569") or ("6566259") or ("6458255") or ("6368880") or ("6627050") or ("6790776") or ("6893541") or ("6793779") or ("6881673") or ("6919275")) .PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:12
2	L2	1271	(427/534,536,537) .CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:13
3	L3	13367	(438/710-733,622,637-640,653) .CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:25

update interference search, etc
09/388, 989

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	L #	Hits	Search Text	DBs	Time Stamp
4	L4	841	(134/1.1,1.2).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:25
5	L5	677879	plasma sputter\$5 (glow corona electric)adj discharg\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:27
6	L6	152616	5 same(clean\$5 preclean\$5 etch\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:29
7	L7	17922	6 same(Ar argon inert adj gas)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:33
8	L8	16655	7 and (Ar argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:34
9	L9	1732	6 same(He helium inert adj gas) same(H2 "H.sub.2" hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:32
10	L10	1394	6 same("He.m/c." helium inert adj gas) same(H2 "H.sub.2" hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:34

3

	L #	Hits	Search Text	DBs	Time Stamp
11	L11	893	10 and ("He.m/c." helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:35
12	L12	680	8 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:33
13	L13	45041	5 same(Ar argon inert adj gas)not 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:34
14	L14	39140	13 and (Ar argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:34
15	L15	5842	5 same("He.m/c." helium inert adj gas) same(H2 "H.sub.2" hydrogen) not10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:35
16	L16	3652	15 and ("He.m/c." helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:35
17	L17	1951	14 and 16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:36

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	L #	Hits	Search Text	DBs	Time Stamp
18	L18	62	2 and (12 or 17)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:36
19	L19	61	2 and (12 or 17) not 1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:36
20	L20	221	3 and (12 or 17 or 18) not 1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:37
21	L21	221	3 and (12 or 17) not (1 or 18)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:38
	L24	145	3 and 12 not (1 or 18)		
22	L22	32	4 and (12 or 17) not (1 or 18 or 21)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:40
23	L23	635	10 same 7 and ("He.m/c." helium)and (Ar argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:44
24	L24	631	23 not 1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:42

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	L #	Hits	Search Text	DBs	Time Stamp
25	L25	471	23 not (1 or 18 Or 21 or 22)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:46
26	L26	214	10 same 7 same (metal barrier Al aluminum Ti titanium) and("He.m/c." helium)and (Ar argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:46
27	L27	160	26 not (1 or 18 or 21 or 22)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:46
28	L28	311	25 not 27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/09/02 13:47

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Day : Friday
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Time: 09:08:34

Inventor Name Search Result

*Inventor Name
Search*

Your Search was:

Last Name = COHEN

First Name = BARNEY

09/388,989

Application#	Patent#	Status	Date Filed	Title	Inventor Name
08400329	5688358	150	03/08/1995	R.F. PLASMA REACTOR WITH LARGER-THAN-WAFER PEDESTAL CONDUCTOR	COHEN, BARNEY
08605507	Not Issued	161	02/26/1996	METHODS FOR SUPPRESSING DETRIMENTAL EFFECTS OF CONDUCTIVE DEPOSITS ON INTERIOR SURFACES OF A PLASMA REACTOR	COHEN, BARNEY
60085854	Not Issued	159	05/18/1998	REDUCTION OF CUO IN A DUAL FREQUENCY ETCH CHAMBER	COHEN, BARNEY M
09388989	Not Issued	135	09/02/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	COHEN, BARNEY M.
10075510	6589890	150	02/12/2002	PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-KAPPA DIELECTRIC	COHEN, BARNEY M.
06534853	Not Issued	161	09/22/1983	SEMICONDUCTOR DEVICES WITHOUT DIFFUSION PIPES	COHEN, BARNEY M.
08252334	Not Issued	169	06/01/1994	INDUCTIVELY COUPLED PLASMA REACTOR WITH TOP ELECTRODE FOR ENHANCING PLASMA IGNITION	COHEN, BARNEY M.
08252963	Not Issued	166	06/02/1994	INDUCTIVELY COUPLED PLASMA REACTOR WITH AN ELECTRODE FOR ENHANCING PLASMA IGNITION	COHEN, BARNEY M.
08561144	5685941	150	11/21/1995	INDUCTIVELY COUPLED PLASMA REACTOR WITH TOP ELECTRODE FOR ENHANCING PLASMA	COHEN, BARNEY M.

				IGNITION	
<u>08646862</u>	<u>5763010</u>	150	05/08/1996	THERMAL POST-DEPOSITION TREATMENT OF HALOGEN-DOPED FILMS TO IMPROVE FILM STABILITY AND REDUCE HALOGEN MIGRATION TO INTERCONNECT LAYERS	COHEN, BARNEY M.
<u>09065758</u>	<u>6079354</u>	150	04/24/1998	THERMAL POST-DEPOSITION TREATMENT OF HALOGEN-DOPED FILMS TO IMPROVE FILM STABILITY AND REDUCE HALOGEN MIGRATION TO INTERCONNECT LAYERS	COHEN, BARNEY M.
<u>09082746</u>	<u>6547934</u>	150	05/21/1998	REDUCTION OF METAL OXIDE IN A DUAL FREQUENCY ETCH CHAMBER	COHEN, BARNEY M.
<u>09088759</u>	<u>6077353</u>	150	06/02/1998	PEDESTAL INSULATOR FOR A PRE-CLEAN CHAMBER	COHEN, BARNEY M.
<u>09206027</u>	Not Issued	61	12/04/1998	PLASMA PRECLEAN WITH ARGON, HELIUM, AND HYDROGEN GASES	COHEN, BARNEY M.
<u>09298065</u>	<u>6110836</u>	150	04/22/1999	REACTIVE PLASMA ETCH-CLEANING OF HIGH ASPECT RATIO OPENINGS	COHEN, BARNEY M. Au 1765
<u>09309606</u>	Not Issued	161	05/11/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	COHEN, BARNEY M.
<u>09378364</u>	Not Issued	161	08/20/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	COHEN, BARNEY M.
<u>09388991</u>	<u>6346489</u>	150	09/02/1999	PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-K DIELECTRIC	COHEN, BARNEY M.
<u>09390135</u>	<u>6313042</u>	150	09/03/1999	CLEANING CONTACT WITH SUCCESSIVE FLUORINE AND HYDROGEN PLASMAS	COHEN, BARNEY M.

Inventor Search Completed: No Records to Display.

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Last Name	First Name	
COHEN	BARNEY	Search

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Day : Friday
 Date: 9/2/2005
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Inventor Name Search Result

Your Search was:

Last Name = LI

First Name = XIANGBING

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09206027	Not Issued	61	12/04/1998	PLASMA PRECLEAN WITH ARGON, HELIUM, AND HYDROGEN GASES	LI, XIANGBING
09218703	6372301	150	12/22/1998	METHOD OF IMPROVING ADHESION OF DIFFUSION LAYERS ON FLUORINATED SILICON DIOXIDE	LI, XIANGBING
09309606	Not Issued	161	05/11/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	LI, XIANGBING
09388989	Not Issued	135	09/02/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	LI, XIANGBING
09414651	6277253	150	10/06/1999	EXTERNAL COATING OF TUNGSTEN OR TANTALUM OR OTHER REFRACTORY METAL ON IMP COILS	LI, XIANGBING
09657792	Not Issued	161	09/08/2000	Method of forming titanium nitride (TiN) films using metal-organic chemical vapor deposition (MOCVD)	LI, XIANGBING
10097413	Not Issued	161	03/12/2002	Adhesion of diffusion barrier and fluorinated silicon dioxide using hydrogen based preclean technology	LI, XIANGBING

Inventor Search Completed: No Records to Display.

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Inventor Name Search Result

Your Search was:

Last Name = RENGARAJAN

First Name = SURAJ

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09309606	Not Issued	161	05/11/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	RENGARAJAN, SURAJ
09362923	6313033	150	07/27/1999	IONIZED METAL PLASMA TA, TANX, W, AND WN X LINERS FOR GATE ELECTRODE APPLICATIONS	RENGARAJAN, SURAJ
09388989	Not Issued	135	09/02/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	RENGARAJAN, SURAJ
09388991	6346489	150	09/02/1999	PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-K DIELECTRIC	RENGARAJAN, SURAJ
09425082	6207558	150	10/21/1999	BARRIER APPLICATIONS FOR ALUMINUM PLANARIZATION	RENGARAJAN, SURAJ
09649507	Not Issued	161	08/28/2000	METHOD AND APPARATUS FOR DEPOSITING A NITROGEN CONTAINING FILM FOR LOW-K APPLICATIONS	RENGARAJAN, SURAJ
09775356	Not Issued	161	01/31/2001	Method of obtaining low temperature alpha-Ta thin films using wafer bias	RENGARAJAN, SURAJ
09784709	6368880	150	02/14/2001	Barrier applications for aluminum planarization	RENGARAJAN, SURAJ
09908829	6579730	150	07/18/2001	MONITORING PROCESS FOR OXIDE REMOVAL	RENGARAJAN, SURAJ
10015433	6908865	150	12/12/2001	METHOD AND APPARATUS FOR CLEANING SUBSTRATES	RENGARAJAN, SURAJ
10075510	6589890	150	02/12/2002	PRECLEANING PROCESS FOR METAL PLUG THAT	RENGARAJAN, SURAJ

				MINIMIZES DAMAGE TO LOW-KAPPA DIELECTRIC	
<u>10186270</u>	<u>6936842</u>	150	06/26/2002 X	METHOD AND APPARATUS FOR PROCESS MONITORING	RENGARAJAN, SURAJ
10202778	Not Issued	161	07/25/2002	Self-ionized and inductively-coupled plasma for sputtering and resputtering	RENGARAJAN, SURAJ
<u>10246316</u>	<u>6911124</u>	150	09/17/2002 T	METHOD OF DEPOSITING A TAN SEED LAYER <i>Ta₂N</i>	RENGARAJAN, SURAJ
10439021	Not Issued	161	05/14/2003	Method and apparatus for sputter deposition	RENGARAJAN, SURAJ
<u>10495506</u>	Not Issued	30	05/12/2004 X	Self-ionized and inductively-coupled plasma for sputtering and resputtering	RENGARAJAN, SURAJ
<u>10942358</u>	Not Issued	30	09/16/2004 X	Compensation of spacing between magnetron and sputter target	RENGARAJAN, SURAJ
<u>11069348</u>	Not Issued	30	02/28/2005 7 1	Method of depositing a tantalum nitride / tantalum-diffusion barrier layer system	RENGARAJAN, SURAJ
<u>11184404</u>	Not Issued	20	07/18/2005 ?	Method of depositing low resistivity barrier layers for copper interconnects	RENGARAJAN, SURAJ
<u>11184615</u>	Not Issued	30	07/19/2005	Self-ionized and inductively-coupled plasma for sputtering and resputtering	RENGARAJAN, SURAJ
<u>60159986</u>	Not Issued	159	10/18/1999	PVD-IMP TUNGSTEN AND TUNGSTEN NITRIDE AS A LINER, BARRIER, AND/OR SEED LAYER FOR TUNGSTEN,ALUMINUM AND COPPER APPLICATIONS	RENGARAJAN, SURAJ
<u>60301179</u>	Not Issued	159	06/27/2001	Method and apparatus for process monitoring	RENGARAJAN, SURAJ
<u>60306698</u>	Not Issued	159	07/20/2001	Low resistivity tantalum nitride/tantalum bilayer stack	RENGARAJAN, SURAJ
<u>60325712</u>	Not Issued	159	09/28/2001	Method and apparatus for plasma cleaning of copper	RENGARAJAN, SURAJ
<u>60342608</u>	Not Issued	159	12/21/2001	Self-ionized and inductively-coupled plasma for sputtering and resputtering	RENGARAJAN, SURAJ
<u>60380385</u>	Not Issued	159	05/14/2002	Method and apparatus for sputter deposition	RENGARAJAN, SURAJ
<u>60529209</u>	Not Issued	159	12/12/2003	Compensation of spacing between magnetron and sputter target	RENGARAJAN, SURAJ

P20.

60701316	Not Issued	20	07/21/2005	Method and apparatus for in-situ substrate surface arc detection	RENGARAJAN, SURAJ
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Inventor Search Completed: No Records to Display.

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	RENGARAJAN	SURAJ	

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Day : Friday
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Inventor Name Search Result

Your Search was:

Last Name = NGAN

First Name = KENNY

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09593848	Not Issued	164	06/14/2000	METHOD AND APPARATUS FOR BALANCING AN ELECTROSTATIC FORCE PRODUCED BY AN ELECTROSTATIC CHUCK	NGAN, KENNY K.
10286688	6625003	150	11/01/2002	METHOD AND APPARATUS FOR BALANCING AN ELECTROSTATIC FORCE PRODUCED BY AN ELECTROSTATIC CHUCK	NGAN, KENNY K.
08312384	5504043	150	09/26/1994	BARRIER LAYERS AND ALUMINUM CONTACTS	NGAN, KENNY K.
08403085	Not Issued	166	03/13/1995	TREATMENT OF A TITANIUM NITRIDE LAYER TO IMPROVE RESISTANCE TO ELEVATED TEMPERATURES	NGAN, KENNY K.
08741708	5961793	150	10/31/1996	METHOD OF REDUCING GENERATION OF PARTICULATE MATTER IN A SPUTTERING CHAMBER	NGAN, KENNY K.
60139710	Not Issued	150	06/17/1999	METHOD AND APPARATUS FOR BALANCING AN ELECTROSTATIC FORCE PRODUCED BY AN ELECTROSTATIC CHUCK	NGAN, KENNY K.
08560083	Not Issued	164	11/17/1995	METHOD FOR SPUTTER ETCHING SILICON WAFER WITH AN ELECTRICALLY CONDUCTING SURFACE AT A REDUCED PRESSURE	NGAN, KENNY K.T.
08569760	5746460	150	12/08/1995	END EFFECTOR FOR SEMICONDUCTOR WAFER TRANSFER DEVICE AND METHOD OF MOVING A WAFER WITH AN END	NGAN, KENNY KING TAI

				EFFECTOR	
08677588	Not Issued	161	07/09/1996	METHOD FOR PROVIDING FULL-FACE HIGH DENSITY PLASMA DEPOSITION	NGAN, KENNY KING-TAI
09388989	Not Issued	135	09/02/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	NGAN, KENNY KING-TAI
09565569	6426282	150	05/04/2000	METHOD OF DEPOSITING LOW STRESS FILMS	NGAN, KENNY KING-TAI
09578007	6267423	250	05/24/2000	End effector for semiconductor wafer transfer device and method of moving a wafer with an end effector	NGAN, KENNY KING-TAI
09597977	Not Issued	161	06/20/2000	Method of producing smooth titanium nitride films having low resistivity	NGAN, KENNY KING-TAI
09695941	6420260	150	10/24/2000	TI/TINX UNDERLAYER WHICH ENABLES A HIGHLY <111> ORIENTED ALUMINUM INTERCONNECT	NGAN, KENNY KING-TAI
10046954	Not Issued	41	01/14/2002	Semiconductor wafer preheating	NGAN, KENNY KING-TAI
10075510	6589890	150	02/12/2002	PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-KAPPA DIELECTRIC	NGAN, KENNY KING-TAI
10097413	Not Issued	161	03/12/2002	Adhesion of diffusion barrier and fluorinated silicon dioxide using hydrogen based preclean technology	NGAN, KENNY KING-TAI
10126333	Not Issued	61	04/19/2002	Reducing particle generation during sputter deposition	NGAN, KENNY KING-TAI
10140732	Not Issued	161	05/07/2002	Method of producing smooth titanium nitride films having low resistivity	NGAN, KENNY KING-TAI
10229879	6672864	150	08/27/2002	METHOD AND APPARATUS FOR PROCESSING SUBSTRATES IN A SYSTEM HAVING HIGH AND LOW PRESSURE AREAS	NGAN, KENNY KING-TAI
10256660	Not Issued	161	09/27/2002	Method for modulating stress in films deposited using a physical vapor deposition (PVD) process	NGAN, KENNY KING-TAI
10748931	Not Issued	168	12/24/2003	Method and apparatus for processing substrates in a system	NGAN, KENNY KING-TAI

				having high and low pressure areas	
<u>10799361</u>	Not Issued	30	03/12/2004	Refurbishment of sputtering targets	NGAN, KENNY KING-TAI
<u>10888941</u>	6945857	150	07/08/2004	POLISHING PAD CONDITIONER AND METHODS OF MANUFACTURE AND RECYCLING	NGAN, KENNY KING-TAI
<u>10901319</u>	Not Issued	30	07/27/2004	Reduced oxygen arc spray	NGAN, KENNY KING-TAI
<u>10910096</u>	Not Issued	30	08/02/2004	Coating for aluminum component	NGAN, KENNY KING-TAI
<u>10962890</u>	Not Issued	41	10/12/2004	Polishing pad conditioner with shaped abrasive patterns and channels	NGAN, KENNY KING-TAI
<u>10968367</u>	Not Issued	30	10/18/2004	In-situ monitoring of target erosion	NGAN, KENNY KING-TAI
<u>11130493</u>	Not Issued	30	05/16/2005	Method and apparatus for improving sidewall coverage during sputtering in a chamber having an inductively coupled plasma	NGAN, KENNY KING-TAI
<u>60316632</u>	Not Issued	159	08/31/2001	Method and apparatus for processing substrates in a system having high and low pressure areas	NGAN, KENNY KING-TAI
<u>07735397</u>	<u>5242860</u>	150	07/24/1991	METHOD FOR THE FORMATION OF TIN BARRIER LAYER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION	NGAN, KENNY KING-TAI
<u>08017081</u>	<u>5378660</u>	150	02/12/1993	BARRIER LAYERS AND ALUMINUM CONTACTS	NGAN, KENNY KING-TAI
<u>08065309</u>	<u>5360996</u>	150	05/21/1993	TITANIUM NITRIDE/TITANIUM SILICIDE MULTIPLE LAYER BARRIER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION ON TITANIUM NITRIDE SURFACE	NGAN, KENNY KING-TAI
<u>08253515</u>	<u>5434044</u>	250	06/03/1994	METHOD FOR THE FORMATION OF TIN BARRIER LAYER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION	NGAN, KENNY KING-TAI
<u>08310180</u>	Not Issued	166	09/21/1994	BARRIER LAYERS AND ALUMINUM CONTACTS	NGAN, KENNY KING-TAI
<u>08377566</u>	<u>5521120</u>	150	01/24/1995	METHOD FOR THE	NGAN, KENNY

				FORMATION OF TIN BARRIER LAYER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION	KING-TAI
08402676	5759360	150	03/13/1995	WAFAER <u>CLEAN SPUTTERING</u> PROCESS	NGAN, KENNY KING-TAI
08481550	5972178	250	06/07/1995	CONTINUOUS PROCESS FOR FORMING <u>IMPROVED</u> TITANIUM NITRIDE BARRIER LAYERS	NGAN, KENNY KING-TAI
08542573	Not Issued	166	10/13/1995	METHOD FOR GENERATING AN EUTECTIC REACTION WITHIN A PHYSICAL VAPOR DEPOSITION SYSTEM	NGAN, KENNY KING-TAI
08551688	Not Issued	166	11/01/1995	BARRIER LAYERS AND ALUMINUM CONTACTS	NGAN, KENNY KING-TAI
08576953	5697427	150	12/22/1995	APPARATUS AND METHOD FOR COOLING A SUBSTRATE	NGAN, KENNY KING-TAI
08682845	5707498	150	07/12/1996	AVOIDING CONTAMINATION FROM INDUCTION COIL IN IONIZED SPUTTERING	NGAN, KENNY KING-TAI
08805181	5919342	250	02/26/1997	METHOD FOR DEPOSITING GOLDEN TITANIUM NITRIDE	NGAN, KENNY KING-TAI
08806966	6071811	150	02/26/1997	DEPOSITION OF TITANIUM NITRIDE FILMS HAVING IMPROVED UNIFORMITY	NGAN, KENNY KING-TAI
08824465	Not Issued	161	03/26/1997	BARRIER LAYERS AND ALUMINUM CONTACTS	NGAN, KENNY KING-TAI
08824911	Not Issued	161	03/27/1997	TI/TIN/TINX UNDERLAYER WHICH ENABLES A HIGHLY (111) ORIENTED ALUMINUM INTERCONNECT	NGAN, KENNY KING-TAI
08825216	5925225	150	03/27/1997	SMOOTH TITANIUM NITRIDE FILMS HAVING LOW RESISTIVITY	NGAN, KENNY KING-TAI
08833404	Not Issued	161	04/04/1997	MEHTOD AND APPARATUS FOR REDUCING THE FIRST WAFER EFFECT	NGAN, KENNY KING-TAI
08840439	5943600	150	03/31/1997	TREATMENT OF A TITANIUM NITRIDE LAYER TO IMPROVE RESISTANCE TO ELEVATED TEMPERATURES	NGAN, KENNY KING-TAI
08847233	6207027	150	05/07/1997	METHOD TO REDUCE OVERHEAD TIME IN AN ION METAL PLASMA PROCESS	NGAN, KENNY KING-TAI

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Application#	Patent#	Status	Date Filed	Title	Inventor Name
08864790	Not Issued	161	05/29/1997	METHOD FOR GENERATING AN EUTECTIC REACTION WITHIN A PHYSICAL VAPOR DEPOSITION SYSTEMS	NGAN, KENNY KING-TAI
08897750	Not Issued	161	07/21/1997	END EFFECTOR FOR SEMICONDUCTOR WAFER TRANSFER DEVICE AND METHOD OF MOVING A WAFER WITH AN END EFFECTOR	NGAN, KENNY KING-TAI
08914580	6176978	150	08/18/1997	PASTING METHOD	NGAN, KENNY KING-TAI
08924487	5882399	150	08/23/1997	METHOD OF FORMING A BARRIER LAYER WHICH ENABLES A CONSISTENTLY HIGHLY ORIENTED CRYSTALLINE STRUCTURE IN A METALLIC INTERCONNECT	NGAN, KENNY KING-TAI
08977007	6045666	150	11/24/1997	ALUMINUM HOLE FILLING METHOD USING IONIZED METAL ADHESION LAYER	NGAN, KENNY KING-TAI
09003014	Not Issued	163	01/05/1998	METHOD OF DEPOSITING A TITANIUM NITRIDE FILM HAVING LOW STRESS AND PROVIDING HIGH BOTTOM COVERAGE IN HIGH ASPECT RATIO FEATURES	NGAN, KENNY KING-TAI
09010359	6059872	150	01/21/1998	SMOOTH TITANIUM NITRIDE FILMS HAVING LOW RESISTIVITY	NGAN, KENNY KING-TAI
09206027	Not Issued	61	12/04/1998	PLASMA PRECLEAN WITH ARGON, HELIUM, AND HYDROGEN GASES	NGAN, KENNY KING-TAI

09218703	6372301	150	12/22/1998	METHOD OF IMPROVING ADHESION OF DIFFUSION LAYERS ON FLUORINATED SILICON DIOXIDE	NGAN, KENNY KING-TAI
09294441	6149777	150	01/25/1999	METHOD OF PRODUCING SMOOTH TITANIUM NITRIDE FILMS HAVING LOW RESISTIVITY	NGAN, KENNY KING-TAI
09298065	6110836	150	04/22/1999	REACTIVE PLASMA ETCH CLEANING OF HIGH ASPECT RATIO OPENINGS	NGAN, KENNY KING-TAI
09309606	Not Issued	161	05/11/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	NGAN, KENNY KING-TAI
09388991	6346489	150	09/02/1999	PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-K DIELECTRIC	NGAN, KENNY KING-TAI
09390135	6313042	150	09/03/1999	CLEANING CONTACT WITH SUCCESSIVE FLUORINE AND HYDROGEN PLASMAS	NGAN, KENNY KING-TAI
09425583	6149784	150	10/22/1999	SPUTTERING CHAMBER SHIELD PROMOTING RELIABLE PLASMA IGNITION	NGAN, KENNY KING-TAI
10263167	6899799	150	10/02/2002	METHOD AND APPARATUS FOR IMPROVING SIDEWALL COVERAGE DURING SPUTTERING IN A CHAMBER HAVING AN INDUCTIVELY COUPLED PLASMA	NGAN, KENNY KING-TAI
10900532	Not Issued	20	07/27/2004	Profile detection and refurbishment of deposition targets	NGAN, KENNY KING-TAI

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Application#	Patent#	Status	Date Filed	Title	Inventor Name
08219131	5622608	150	05/05/1994 7	PROCESS OF MAKING OXIDATION RESISTANT HIGH CONDUCTIVITY COPPER LAYERS	DING, PEIJUN
08478491	5766379	150	06/07/1995 7	PASSIVATED COPPER CONDUCTIVE LAYERS FOR MICROELECTRONIC APPLICATIONS AND METHODS OF MANUFACTURING SAME	DING, PEIJUN
08677760	5736021	150	07/10/1996 X	ELECTRICALLY FLOATING SHIELD IN A PLASMA REACTOR	DING, PEIJUN
08756468	Not Issued	168	11/26/1996	COATED DEPOSITION CHAMBER EQUIPMENT	DING, PEIJUN
08761584	Not Issued	161	12/06/1996	MODIFIED PHYSICAL VAPOR DEPOSITION CHAMBER AND METHOD OF DEPOSITING MATERIALS AT LOW PRESSURE	DING, PEIJUN
08820512	5911113	150	03/18/1997 7	SILICON-DOPED TITANIUM WETTING LAYER FOR ALUMINUM PLUG	DING, PEIJUN
08837770	5959358	150	04/22/1997 7	OXIDATION RESISTANT HIGH CONDUCTIVITY COPPER LAYERS FOR MICROELECTRONIC APPLICATIONS AND PROCESS OF MAKING SAME	DING, PEIJUN
08841058	6057237	150	04/29/1997 7	TANTALUM-CONTAINING BARRIER LAYERS FOR COPPER	DING, PEIJUN
08853191	6037257	150	05/08/1997 7	SPUTTER DEPOSITION AND ANNEALING OF COPPER	DING, PEIJUN

				ALLOY METALLIZATION	
08854008	6692617	150	05/08/1997	SUSTAINED SELF-SPUTTERING REACTOR HAVING AN INCREASED DENSITY PLASMA	DING, PEIJUN
08855059	6605197	150	05/13/1997	METHOD OF SPUTTERING COPPER TO FILL TRENCHES AND VIAS	DING, PEIJUN
08863451	6139699	150	05/27/1997	SPUTTERING METHODS FOR DEPOSITING STRESS TUNABLE TANTALUM AND TANTALUM NITRIDE FILMS	DING, PEIJUN
08878143	6387805	150	06/18/1997	COPPER-ALLOY SEED LAYER FOR COPPER METALLIZATION	DING, PEIJUN
08939396	5879523	150	09/29/1997	CERAMIC COATED METALLIC INSULATOR PARTICULARLY USEFUL IN A PLASMA SPUTTER REACTOR	DING, PEIJUN
08978792	Not Issued	161	11/26/1997	DAMAGE-FREE SCULPTURED COATING DEPOSITION	DING, PEIJUN
08995108	6887353	150	12/19/1997	TAILORED BARRIER LAYER WHICH PROVIDES IMPROVED COPPER INTERCONNECT ELECTROMIGRATION RESISTANCE	DING, PEIJUN
09013823	6110821	150	01/27/1998	METHOD FOR FORMING TITANIUM SILICIDE IN SITU	DING, PEIJUN
09021666	6057223	150	02/10/1998	PASSIVATED COPPER CONDUCTIVE LAYERS FOR MICROELECTRONIC APPLICATIONS	DING, PEIJUN
09024530	6077404	150	02/17/1998	REFLOW CHAMBER AND PROCESS	DING, PEIJUN
09039695	6506287	150	03/16/1998	OVERLAP DESIGN OF ONE-TURN COIL	DING, PEIJUN
09047107	Not Issued	163	03/24/1998	TANTALUM-CONTAINING BARRIER LAYERS FOR COPPER	DING, PEIJUN
09058432	Not Issued	161	04/10/1998	BARRIER LAYERS FOR COPPER	DING, PEIJUN
09123010	Not Issued	161	07/27/1998	SPUTTERING TARGET ASSEMBLY	DING, PEIJUN
09160638	Not Issued	161	09/24/1998	ULTRA-LOW RESISTIVITY TANTALUM FILMS AND	DING, PEIJUN

				METHODS FOR THEIR DEPOSITION	
09191078	Not Issued	161	11/12/1998	TANTALUM-CONTAINING BARRIER LAYERS FOR COPPER USING HIGH PURITY TANTALUM TARGETS FOR SPUTTERING	DING, PEIJUN
09191253	6149776	150	11/12/1998 N	COPPER SPUTTERING TARGET	DING, PEIJUN
09199965	6184137	250	11/25/1998 N	STRUCTURE AND METHOD FOR IMPROVING LOW TEMPERATURE COPPER REFLOW IN SEMICONDUCTOR FEATURES	DING, PEIJUN
09204323	6174811	250	12/02/1998 7	INTEGRATED DEPOSITION PROCESS FOR COPPER METALLIZATION	DING, PEIJUN
09208663	Not Issued	161	12/10/1998	HIGH-DENSITY METAL SPUTTERING AT LOW PRESSURE	DING, PEIJUN
09253585	Not Issued	161	02/19/1999	USING ELECTROPLATED CU AS COLD LAYER FOR COLD/HOT DEPOSITION	DING, PEIJUN
09261700	6193811	150	03/03/1999 N	METHOD FOR IMPROVED CHAMBER BAKE-OUT AND COOL-DOWN	DING, PEIJUN
09309606	Not Issued	161	05/11/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	DING, PEIJUN
09326395	6277198	150	06/04/1999 X	USE OF TAPERED SHADOW CLAMP RING TO PROVIDE IMPROVED PHYSICAL VAPOR DEPOSITION SYSTEM	DING, PEIJUN
09328117	6232665	250	06/08/1999 ?	SILICON-DOPED TITANIUM WETTING LAYER FOR ALUMINUM PLUG	DING, PEIJUN
09350556	6235163	250	07/09/1999 ?	METHODS AND APPARATUS FOR IONIZED METAL PLASMA COPPER DEPOSITION WITH ENHANCED IN-FILM PARTICLE PERFORMANCE	DING, PEIJUN
09350619	6376807	150	07/09/1999 X	ENHANCED COOLING IMP COIL SUPPORT	DING, PEIJUN
09362923	6313033	150	07/27/1999 X	IONIZED METAL PLASMA TA, TANX, W, AND WN X LINERS FOR GATE	DING, PEIJUN

				ELECTRODE APPLICATIONS	
09373103	Not Issued	161	08/12/1999	METHOD AND APPARATUS FOR CLEANING A CHAMBER CONFIGURED FOR COPPER DEPOSITION	DING, PEIJUN
09375167	6328871	150	08/16/1999 7X	BARRIER LAYER FOR ELECTROPLATING PROCESSES	DING, PEIJUN
09378364	Not Issued	161	08/20/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	DING, PEIJUN
09386077	6399479	150	08/30/1999 7	NEW PROCESSES TO IMPROVE ELECTROPLATING FILL	DING, PEIJUN
09388989	Not Issued	135	09/02/1999	SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS	DING, PEIJUN
09414614	6398929	150	10/08/1999 7X	PLASMA REACTOR AND SHIELDS GENERATING SELF-IONIZED PLASMA FOR SPUTTERING	DING, PEIJUN
09423470	6488823	150	11/04/1999 7X	STRESS TUNABLE TANTALUM AND TANTALUM NITRIDE FILMS	DING, PEIJUN
09425082	6207558	150	10/21/1999	BARRIER APPLICATIONS FOR ALUMINUM PLANARIZATION	DING, PEIJUN
09430998	6200433	150	11/01/1999 77	IMP TECHNOLOGY WITH HEAVY GAS SPUTTERING	DING, PEIJUN
09440679	6458251	150	11/16/1999 7	PRESSURE MODULATION METHOD TO OBTAIN IMPROVED STEP COVERAGE OF SEED LAYER	DING, PEIJUN
09441032	Not Issued	161	11/16/1999	METHOD AND APPARATUS FOR PHYSICAL VAPOR DEPOSITION USING MODULATED POWER	DING, PEIJUN
09449202	6350353	150	11/24/1999 7	ALTERNATE STEPS OF IMP AND SPUTTERING PROCESS TO IMPROVE SIDEWALL COVERAGE	DING, PEIJUN
09478721	6160315	150	01/06/2000 7X	COPPER ALLOY VIA STRUCTURE	DING, PEIJUN

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Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>09524239</u>	6299689	150	03/13/2000 C	Reflow chamber and process	DING, PEIJUN
<u>09538343</u>	6607640	150	03/29/2000 A	TEMPERATURE CONTROL OF A SUBSTRATE	DING, PEIJUN
<u>09561039</u>	Not Issued	161	04/28/2000	Method and apparatus for reducing overhang in ionized metal plasma systems	DING, PEIJUN
<u>09611624</u>	Not Issued	161	07/07/2000	Stress tunable tantalum and tantalum nitride films	DING, PEIJUN
<u>09618364</u>	Not Issued	161	07/18/2000	TEMPERATURE CONTROLLED SPUTTERING OF LOW COMPRESSIVE STRESS BARRIER LAYERS	DING, PEIJUN
<u>09626850</u>	Not Issued	161	07/27/2000	Tantalum-containing barrier layers for copper using high purity tantalum targets for sputtering	DING, PEIJUN
<u>09649507</u>	Not Issued	161	08/28/2000	METHOD AND APPARATUS FOR DEPOSITING A NITROGEN CONTAINING FILM FOR LOW-K APPLICATIONS	DING, PEIJUN
<u>09650108</u>	6436267	150	08/29/2000	METHOD FOR ACHIEVING COPPER FILL OF HIGH ASPECT RATIO INTERCONNECT FEATURES	DING, PEIJUN
<u>09685978</u>	6582569	150	10/10/2000 3	PROCESS FOR SPUTTERING COPPER IN A SELF IONIZED PLASMA	DING, PEIJUN
<u>09685988</u>	6413383	150	10/10/2000 A	METHOD FOR IGNITING A PLASMA IN A SPUTTER REACTOR	DING, PEIJUN
<u>09691687</u>	Not Issued	161	10/18/2000	PVD-IMP tungsten and tungsten nitride as a liner, barrier, and/or seed layer for tungsten, aluminum	DING, PEIJUN

				and copper applications	
09709991	6352926	150	11/10/2000	Structure for improving low temperature copper reflow in semiconductor features	DING, PEIJUN
09710383	6566259	150	11/09/2000	INTEGRATED-DEPOSITION PROCESS FOR COPPER METALLIZATION	DING, PEIJUN
09725595	6375743	150	11/29/2000	METHOD FOR IMPROVED CHAMBER BAKE-OUT AND COOL-DOWN	DING, PEIJUN
09770934	6458255	150	01/25/2001	ULTRA-LOW RESISTIVITY TANTALUM FILMS AND METHODS FOR THEIR DEPOSITION	DING, PEIJUN
09775356	Not Issued	161	01/31/2001	Method of obtaining low temperature alpha-Ta thin films using wafer bias	DING, PEIJUN
09784709	6368880	150	02/14/2001	Barrier applications for aluminum planarization	DING, PEIJUN
09805865	Not Issued	161	03/13/2001	Integrated barrier layer structure for copper contact level metallization	DING, PEIJUN
09829547	Not Issued	161	04/09/2001	Burn-in process for high density plasma PVD chamber	DING, PEIJUN
09886439	6758947	150	06/20/2001	DAMAGE-FREE SCULPTURED COATING DEPOSITION	DING, PEIJUN
09908829	6579730	150	07/18/2001	MONITORING PROCESS FOR OXIDE REMOVAL	DING, PEIJUN
09916412	6627050	150	07/26/2001	METHOD AND APPARATUS FOR DEPOSITING A TANTALUM-CONTAINING LAYER ON A SUBSTRATE	DING, PEIJUN
09993543	6610184	150	11/14/2001	MAGNET ARRAY IN CONJUNCTION WITH ROTATING MAGNETRON FOR PLASMA SPUTTERING	DING, PEIJUN
10016255	6790776	150	12/10/2001	BARRIER LAYER FOR ELECTROPLATING PROCESSES	DING, PEIJUN
10016350	6580057	150	12/10/2001	ENHANCED COOLING IMP COIL SUPPORT	DING, PEIJUN
10037172	Not Issued	161	11/07/2001	Alternate steps of IMP and sputtering process to improve sidewall coverage	DING, PEIJUN
10060827	Not	161	01/29/2002	Stress tunable tantalum and	DING, PEIJUN

	Issued			tantalum nitride films	
10146416	Not Issued	161	05/14/2002	METHODS OF PRODUCING ULTRA -LOW RESISTIVITY TANTALUM FILMS.	DING, PEIJUN
10152494	6841050	150	05/21/2002	SMALL PLANETARY MAGNETRON	DING, PEIJUN
10180225	Not Issued	161	06/26/2002	Method for achieving copper fill of high aspect ratio interconnect features	DING, PEIJUN
10202778	Not Issued	161	07/25/2002	Self-ionized and inductively-coupled plasma for sputtering and resputtering	DING, PEIJUN
10246316	6911124	150	09/17/2002	METHOD OF DEPOSITING A TAN SEED LAYER	DING, PEIJUN
10262652	Not Issued	41	09/30/2002	Pressure modulation method to obtain improved step coverage of seed layer	DING, PEIJUN
10326496	6893541	150	12/20/2002	MULTI-STEP PROCESS FOR DEPOSITING COPPER SEED LAYER IN A VIA	DING, PEIJUN
10369856	6793779	150	02/20/2003	SPUTTERING METHOD FOR FILLING HOLES WITH COPPER	DING, PEIJUN
10418710	6852202	150	04/17/2003	SMALL EPICYCLIC MAGNETRON WITH CONTROLLED RADIAL SPUTTERING PROFILE	DING, PEIJUN
10421174	6881673	150	04/22/2003	INTEGRATED DEPOSITION PROCESS FOR COPPER METALLIZATION	DING, PEIJUN
10439021	Not Issued	161	05/14/2003	Method and apparatus for sputter deposition	DING, PEIJUN
10495506	Not Issued	30	05/12/2004	Self-ionized and inductively-coupled plasma for sputtering and resputtering	DING, PEIJUN
10608306	Not Issued	61	06/26/2003	Sidewall magnet improving uniformity of inductively coupled plasma and shields used therewith	DING, PEIJUN
10643281	Not Issued	41	08/18/2003	One or more shields for use in a sputter reactor	DING, PEIJUN
10646014	6875321	150	08/22/2003	AUXILIARY MAGNET ARRAY IN CONJUNCTION WITH MAGNETRON SPUTTERING	DING, PEIJUN
10755644	Not Issued	92	01/12/2004	ROTATIONAL AND RECIPROCAL RADIAL	DING, PEIJUN

				MOVEMENT OF A SPUTTERING MAGNETRON	
<u>10796602</u>	<u>6919275</u>	<u>150</u>	03/08/2004 7	METHOD OF PREVENTING DIFFUSION OF COPPER THROUGH A TANTALUM-COMPRISING BARRIER LAYER	DING, PEIJUN
<u>10862257</u>	Not Issued	61	06/07/2004 X	Magnetron executing planetary motion adjacent a sputtering target	DING, PEIJUN
<u>10915139</u>	Not Issued	30	08/09/2004 ?	Sputter deposition and etching of metallization seed layer for overhang and sidewall improvement	DING, PEIJUN
<u>10922052</u>	Not Issued	30	08/18/2004 ?	Method of depositing a diffusion barrier layer and a metal conductive layer	DING, PEIJUN
<u>10931865</u>	Not Issued	41	09/01/2004 ?	Barrier layer for electroplating processes	DING, PEIJUN
<u>10940518</u>	Not Issued	41	09/14/2004 ?	TWO STEP METHOD FOR FILLING HOLES WITH COPPER	DING, PEIJUN
<u>10942273</u>	Not Issued	30	09/16/2004 X	Mechanism for varying the spacing between sputter magnetron and target	DING, PEIJUN

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Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>10942358</u>	Not Issued	30	09/16/2004	Compensation of spacing between magnetron and sputter target	DING, PEIJUN
<u>10981319</u>	Not Issued	30	11/03/2004	Method of depositing a metal seed layer on semiconductor substrates	DING, PEIJUN
<u>11069348</u>	Not Issued	30	02/28/2005	Method of depositing a tantalum nitride / tantalum diffusion barrier layer system	DING, PEIJUN
<u>11124524</u>	Not Issued	30	05/05/2005	Shields usable with an inductively coupled plasma reactor.	DING, PEIJUN
<u>11184404</u>	Not Issued	20	07/18/2005	Method of depositing low resistivity barrier layers for copper interconnects	DING, PEIJUN
<u>11184615</u>	Not Issued	30	07/19/2005	Self-ionized and inductively-coupled plasma for sputtering and resputtering	DING, PEIJUN
<u>29090631</u>	<u>D440582</u>	150	07/13/1998	SPUTTERING CHAMBER COIL	DING, PEIJUN
<u>60067108</u>	Not Issued	159	12/02/1997	INTEGRATED DEPOSITION PROCESS FOR COPPER METALLIZATION	DING, PEIJUN
<u>60159986</u>	Not Issued	159	10/18/1999	PVD-IMP TUNGSTEN AND TUNGSTEN NITRIDE AS A LINER, BARRIER, AND/OR SEED LAYER FOR TUNGSTEN, ALUMINUM AND COPPER APPLICATIONS	DING, PEIJUN
<u>60221597</u>	Not Issued	159	07/28/2000	SIP TA/TAN barrier layer for copper metallization	DING, PEIJUN
<u>60284496</u>	Not Issued	159	04/18/2001	Process for depositing metal seed layer on a substrate	DING, PEIJUN
<u>60306698</u>	Not Issued	159	07/20/2001	Low resistivity tantalum nitride/tantalum bilayer stack	DING, PEIJUN
<u>60316137</u>	Not	159	08/30/2001	Self-ionized and inductively-	DING, PEIJUN

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	Issued			coupled plasma for sputtering	
60342608	Not Issued	159	12/21/2001	Self-ionized and inductively-coupled plasma for sputtering and resputtering	DING, PEIJUN
60380385	Not Issued	159	05/14/2002	Method and apparatus for sputter deposition	DING, PEIJUN
60441866	Not Issued	159	01/22/2003	Small epicyclic magnetron with controlled radial sputtering profile	DING, PEIJUN
60465556	Not Issued	159	04/25/2003	Diode laser systems with multiple wavelengths for skin rejuvenation and other dermatological applications	DING, PEIJUN
60465557	Not Issued	159	04/25/2003	Diode laser systems with multiple wavelengths for hair removal, pigmented lesion and vascular lesion treatment	DING, PEIJUN
60529209	Not Issued	159	12/12/2003	Compensation of spacing between magnetron and sputter target	DING, PEIJUN

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